

PRELIMINARY

Notice : This is not a final specification
Some parametric are subject to change.

INJ0303CC1

High Speed Switching
Silicon P-channel MOSFET

DESCRIPTION

INJ0303CC1 is a Silicon P-channel MOSFET.

This product is most suitable for use such as portable machinery, because of low voltage drive and low on resistance.

FEATURE

- Input impedance is high, and not necessary to consider a drive electric current.
- High drain current $I_D = -3.2A$
- Drive voltage $-2.5V$
- Low on Resistance. $R_{DS(ON)} = 65m\Omega$ typ(@ $V_{GS} = -4.5V$)
 $R_{DS(ON)} = 102m\Omega$ typ(@ $V_{GS} = -2.5V$)
 $R_{DS(ON)} = 174m\Omega$ typ(@ $V_{GS} = -1.8V$)
- High speed switching.

APPLICATION

High speed switching, Analog switching

MAXIMUM RATINGS ($T_a = 25^\circ C$)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-12	V
Gate-Source Voltage	V_{GS}	± 8	V
Drain Current(DC)	I_D	-3.2	A
Drain Current(Pulse) (※1)	I_{DP}	-14	A
Total Power Dissipation (※2)	P_D	0.9	W
Junction Temperature	T_j	+150	$^\circ C$
Storage Temperature	T_{stg}	-55~+150	$^\circ C$

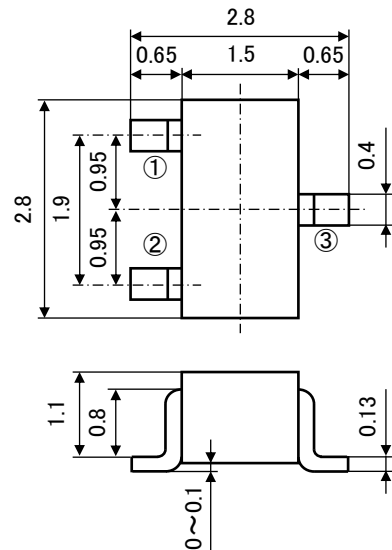
※1 $P_w \leq 1ms$, Duty cycle $\leq 1\%$

※2 package mounted on glass-epoxy substrate.

(39mm × 39mm × 1.6mm, Cu pad 1500mm²)

OUTLINE DRAWING

Unit: mm



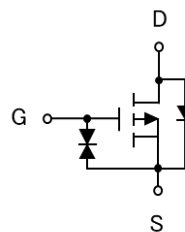
TERMINAL CONNECTOR

- ①: GATE
- ②: SOURCE
- ③: DRAIN

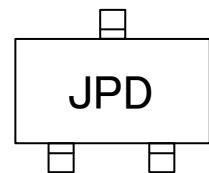
JEITA: SC-59

JEDEC: Similar to TO-236

EQUIVALENT CIRCUIT



MARKING



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	$V_{(BR)DS}$	$I_D = -250\mu A, V_{GS} = 0V$	-12	-	-	V
Gate-Source Leak Current	I_{GSS}	$V_{GS} = \pm 8V, V_{DS} = 0V$	-	-	± 10	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -12V, V_{GS} = 0V$	-	-	-1.0	μA
Gate Threshold Voltage	V_{th}	$I_D = -250\mu A, V_{DS} = V_{GS}$	-0.4	-	-1.2	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$I_D = -3.2A, V_{GS} = -4.5V$	-	65	84	$m\Omega$
		$I_D = -3.2A, V_{GS} = -2.5V$	-	102	142	
		$I_D = -1.0A, V_{GS} = -1.8V$	-	174	295	
Input Capacitance	C_{iss}	$V_{DS} = -10V, V_{GS} = 0V, f = 1MHz$	-	640	-	pF
Output Capacitance	C_{oss}		-	200	-	
Reverse Transfer Capacitance	C_{rss}		-	165	-	
Switching Time	t_{on}	$V_{DD} = -12V, I_D = -200mA, V_{GS} = -5V$	-	40	-	ns
	t_{off}		-	220	-	

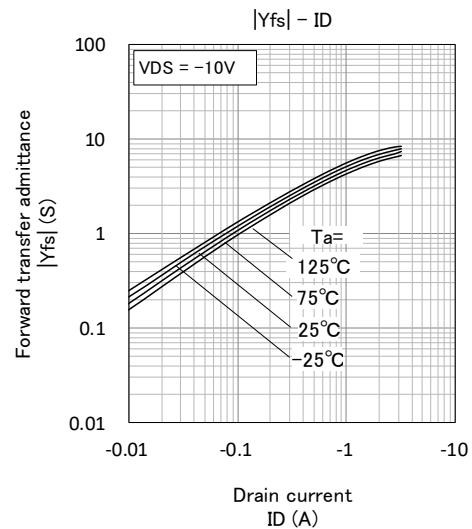
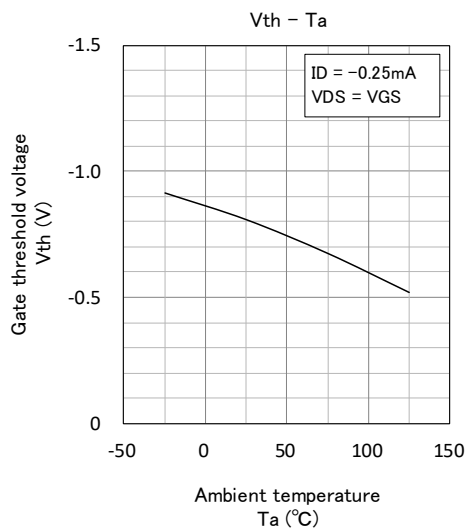
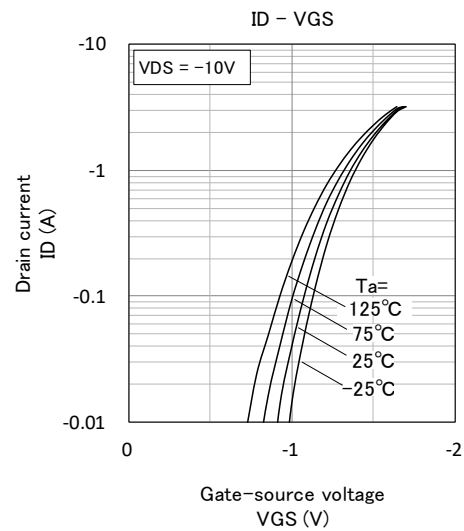
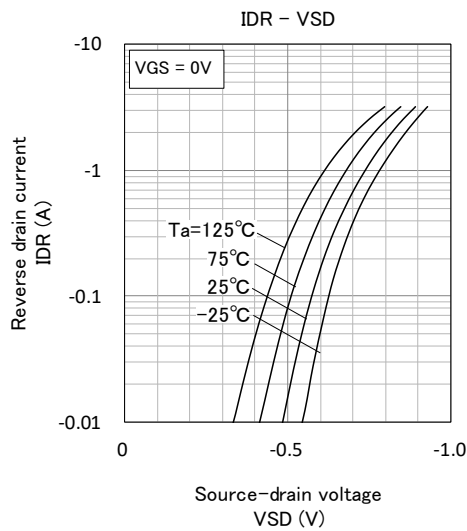
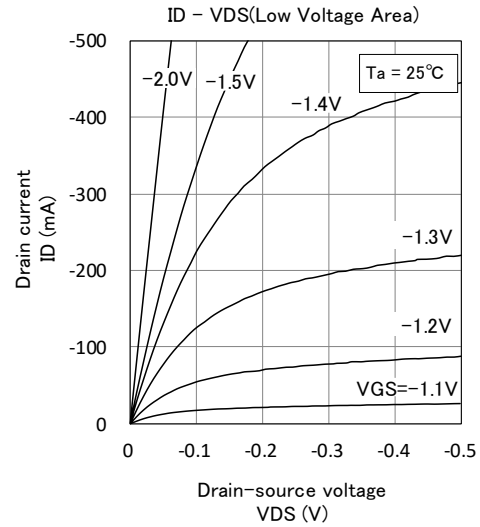
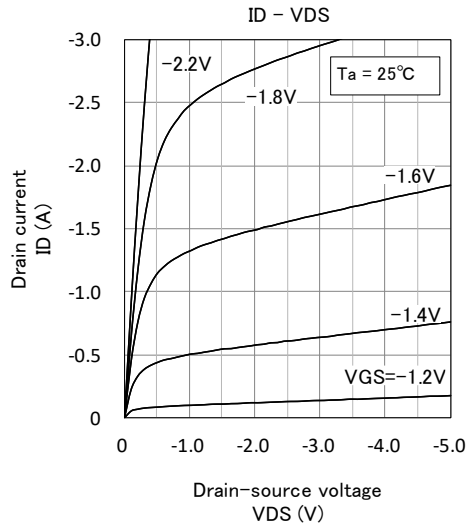
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TYPICAL CHARACTERISTICS

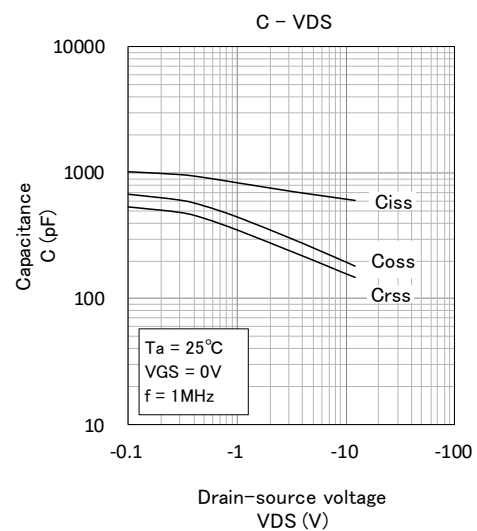
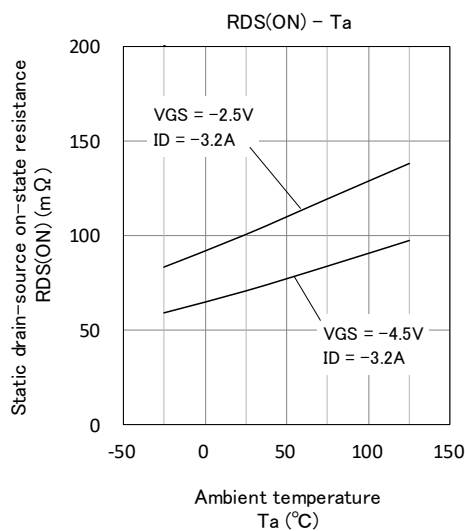
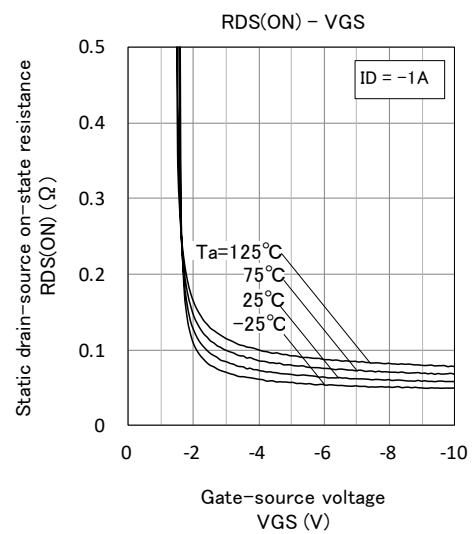
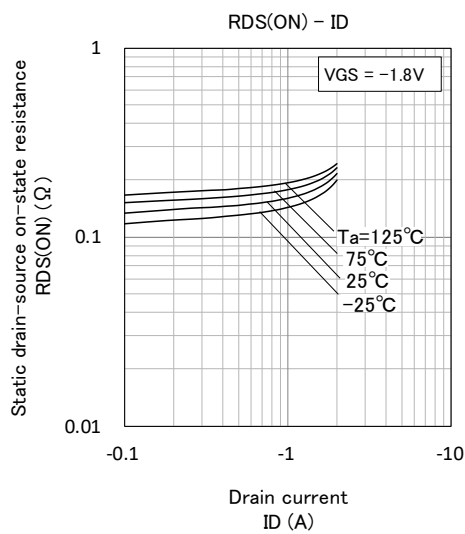
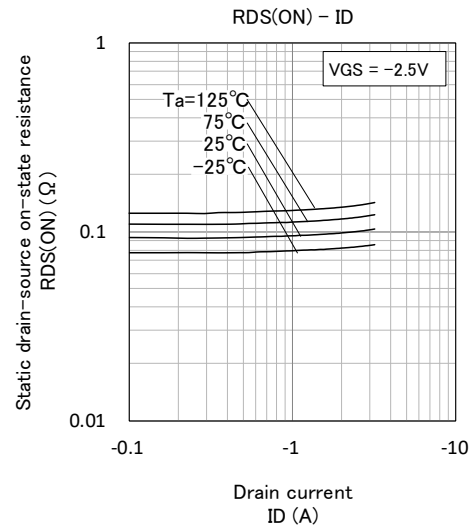
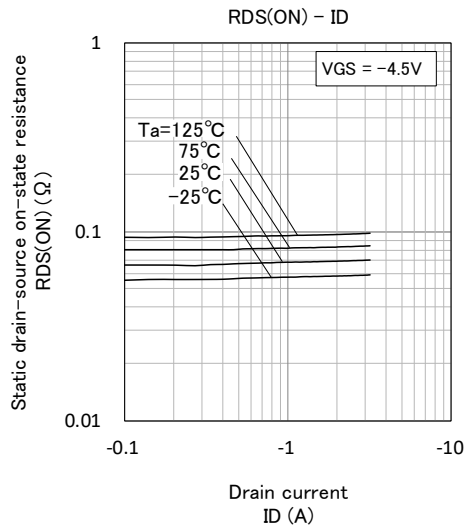


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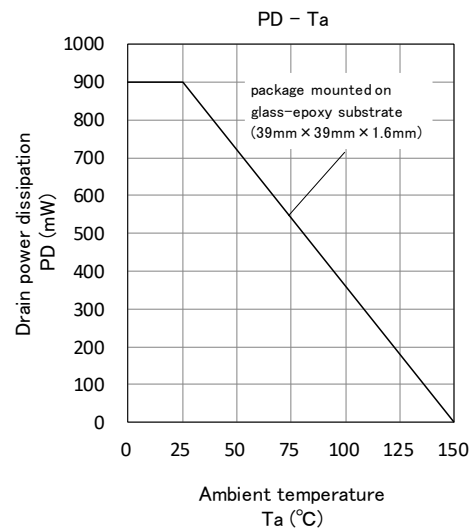
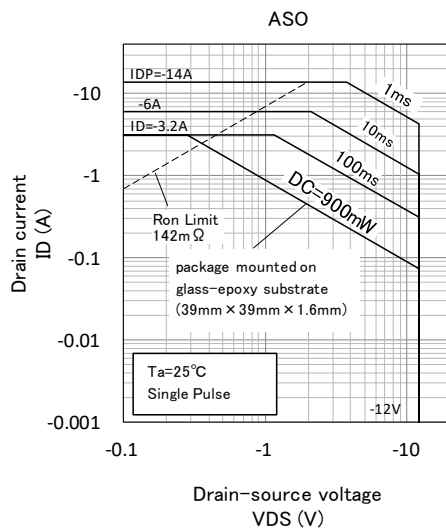
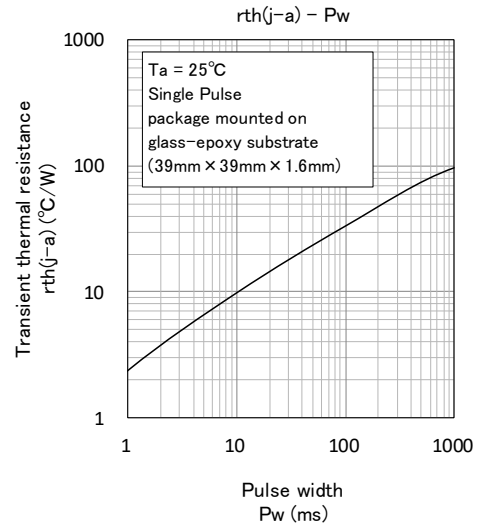
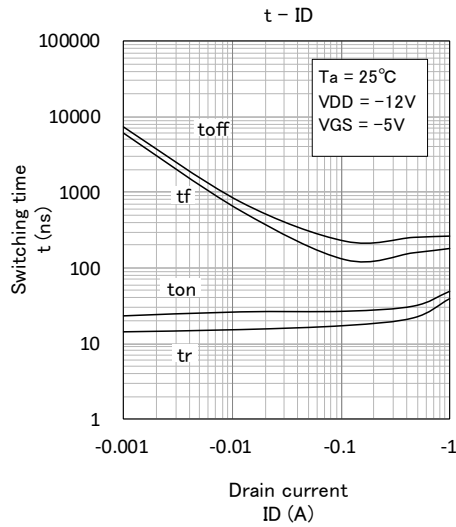


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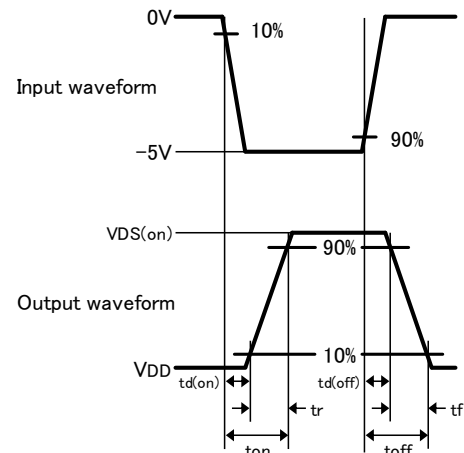
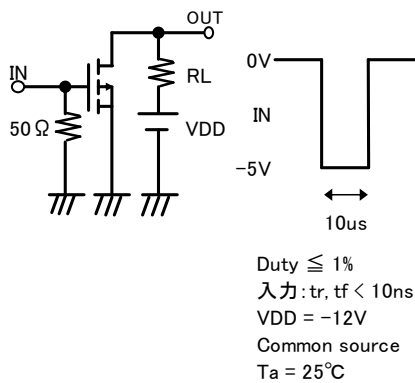
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Switching time test condition



Keep safety first in your circuit designs!

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